# SK 50 B 06 UF



# SEMITOP<sup>® 2</sup>

#### **Bridge Rectifier**

#### SK 50 B 06 UF

Target Data

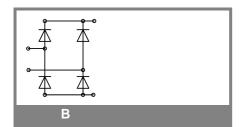
#### Features

- Compact design
- One screw mounting
- Heat transfer and insulation through direct copper bonded aluminium oxide ceramic (DCB)
- Ultra Fast diodes
- UL recognized, file no. E 63 532

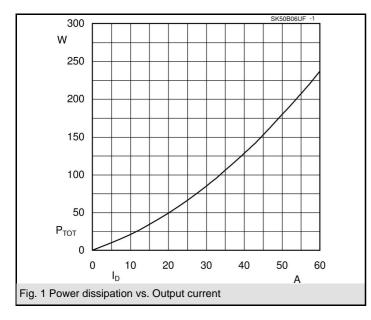
#### **Typical Applications**

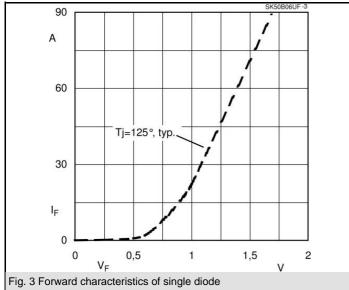
- · General power switching applications
- UPS SMPS
- Welding equipment

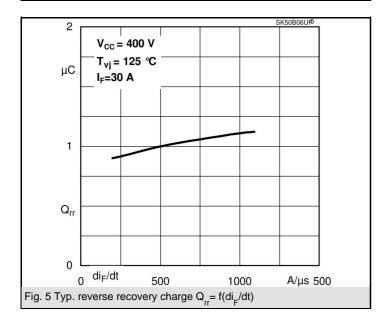
V <sub>RSM</sub>		V <sub>RRM</sub> , V <sub>DRM</sub>		I <sub>D</sub> = 46 A (full conduction)	
V		V		(T <sub>s</sub> = 80 °C)	
600		600		SK 50 B 06 UF	
Oursels al	0.0			Values	l lucito
Symbol		Conditions		Values	Units
I <sub>D</sub>	$T_s = 80 °C$ T = 125°C·V = 400V/1 = 30A		۸.	46 11	A
I <sub>RRM</sub>	T <sub>vj</sub> =125°C;V <sub>R</sub> =400V;I <sub>F</sub> =30A - dI <sub>F</sub> /dt=300A/µs		A;		A
Q <sub>rr</sub>				typ. 0,93	μC
I <sub>R</sub>		25 (150)°C; V <sub>R</sub> =V <sub>RRM</sub>		max 0,015 (0,475)	mA
I <sub>FSM</sub>		150 °C; 10 ms		400	А
.24		°C; ms		222	A
i²t		150 °C; 10 ms		800	A²s
	• 1	°C; ms			A²s
V <sub>F</sub>		125 °C; I <sub>F</sub> = 50 A		max. 1,95	V
V <sub>(TO)</sub>		125 °C		max. 0,8	V
r <sub>T</sub>		125 °C		max. 11	mΩ
I <sub>RD</sub>	T <sub>vj</sub> =	°C; $V_{DD} = V_{DRM}$ ; $V_{RD}$	= V <sub>RRM</sub>		mA
					mA
R <sub>th(j-s)</sub>	per d	liode		1,8	K/W
11(10)	per n	nodule		0,45	K/W
T <sub>solder</sub>	terminals, 10s			260	°C
T <sub>vi</sub>				-40+150	°C
T <sub>stg</sub>				-40+125	°C
V <sub>isol</sub>	a. c.	50 Hz; r.m.s.; 1 s / 1 r	nin.	3000 ( 2500 )	V
M <sub>s</sub>		nting torque to heatsir		2	Nm
M <sub>t</sub>					
m	approx. weight			19	g
Case	Case SEMITOP <sup>®</sup> 2			Т 6	



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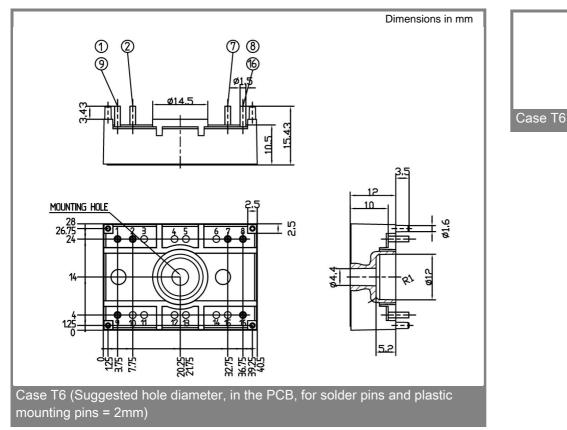






2

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